

Please amend the subject application as follows:

IN THE SPECIFICATION:

Please amend the title of the invention, as follows:

--THIN FILM TRANSISTOR ARRAY PANEL INCLUDING SYMMETRICALLY
ALIGNED THIN FILM TRANSISTORS AND MANUFACTURING METHOD
THEREOF--

Please amend the paragraph beginning at page 5, line 21 and ending at page 5, line 25 as follows:

--A plurality of gate lines 121 for transmitting gate signals are formed on an insulating substrate 110. Each gate line 121 extends substantially in a transverse direction and a plurality of upwardly protruding portions of each gate line 121 form a plurality of gate electrodes 123. The gate electrodes 123 include two gate members 1231 and 1232. Each gate line 121 includes a plurality of expansions protruding downward.--

Please amend the paragraph beginning at page 6, line 10 and ending at page 6, line 15 as follows:

--A plurality of semiconductor stripes 150 preferably made of hydrogenated amorphous silicon (abbreviated to "a-Si") are formed on the gate insulating layer 140. Each semiconductor stripe 150 extends substantially in a longitudinal direction and has a plurality of projections branched out toward the gate electrodes 123. Each semiconductor stripe 150 includes two semiconductor members 1501 and 1502.

The width of each semiconductor stripe 150 becomes large near the gate lines 121 such that the semiconductor stripe 150 covers large areas of the gate lines 121.--

Please amend the paragraph beginning at page 6, line 27 and ending at page 7, line 13 as follows:

--The data lines 171 for transmitting data voltages extend substantially in the longitudinal direction and intersect the gate lines 121. A plurality of branches 1731 and 1732 of each data line 171, which project toward the drain electrodes 175, form a plurality of source electrodes 173. Each drain electrode 175 has two ~~projections~~ drain members 1751 and 1752 extending parallel to each other in the transverse direction and located on the gate electrode 123, and each source electrode 173 has three branches 1731 and 1732 forming two source members 173a and 173b having a twin-semicircle shape partly surrounding the respective ~~projections~~ drain members 1751 and 1752 of the drain electrode 175. The branches 1731 and 1732 extend substantially parallel to the ~~projections~~ drain members 1751 and 1752 in the transverse direction. The ~~branches 1731 and 1732~~ source members 173a and 173b of a source electrode 173, the ~~projections~~ drain members 1751 and 1752 of a drain electrode 175, ~~portions~~ the gate members 1231 and 1232 of a gate electrode 123 located therebetween along with ~~portions~~ the semiconductor members 1501 and 1502 of a semiconductor stripe 150 and portions 1631, 1632, 1651 and 1652 form twin TFTs TFT1 and TFT2 connected in parallel. The planar shape of the twin TFTs TFT1 and TFT2 are symmetrical to the middle branch 1732 of the source electrode ~~[[175]]~~ 173. Since twin transistors TFT1 and TFT2 have U shaped channels, their channel widths are increased such that they have high current driving capacity.--